



STP45NF06 STB45NF06

N-channel 60V - 0.022Ω - 38A TO-220/D²PAK
STripFET™ II Power MOSFET

General features

Type	V _{DSS}	R _{DS(on)}	I _D
STP45NF06	60V	<0.028Ω	38A
STB45NF06	60V	<0.028Ω	38A

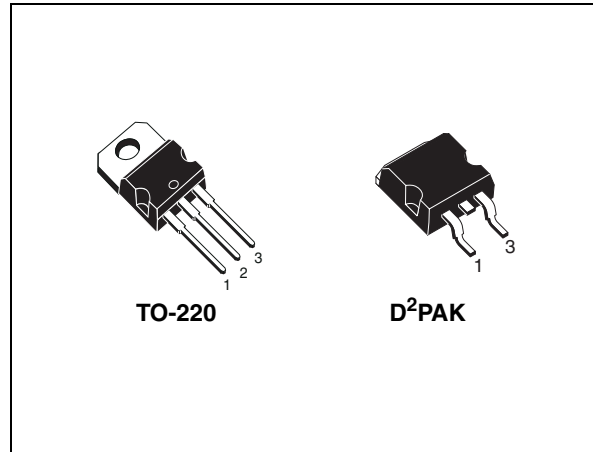
- Exceptional dv/dt capability
- Standard threshold drive
- 100% avalanche tested

Description

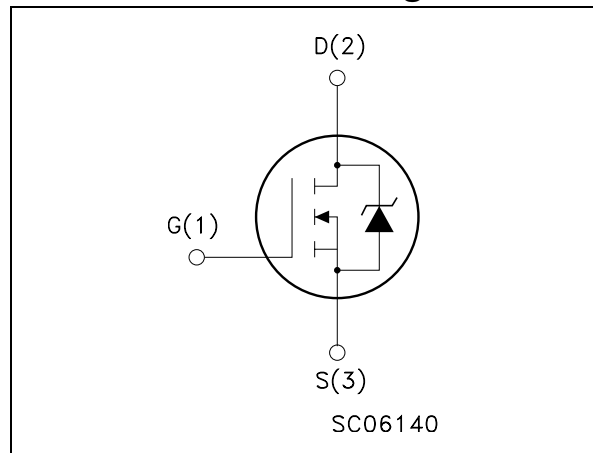
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

Applications

- Switching application



Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STP45NF06	P45NF06	TO-220	Tube
STB45NF06	B45NF06	D ² PAK	Tape & reel

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1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	60	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$	38	A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	26	A
$I_{DM}^{(1)}$	Drain current (pulsed)	152	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	80	W
	Derating factor	0.53	W/ $^\circ\text{C}$
$dv/dt^{(2)}$	Peak diode recovery voltage slope	8	V/ns
T_J	Operating junction temperature	-65 to 175	$^\circ\text{C}$
T_{stg}	Storage temperature	175	$^\circ\text{C}$

1. Pulse width limited by safe operating area

2. $I_{SD} \leq 38\text{A}$, $di/dt \leq 300\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq T_{JMAX}$.

Table 2. Thermal data

$R_{thj-case}$	Thermal resistance junction-case max	1.87	$^\circ\text{C}/\text{W}$
R_{thj-a}	Thermal resistance junction-ambient max	62.5	$^\circ\text{C}/\text{W}$
T_I	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_J Max)	38	A
E_{AS}	Single pulse avalanche energy (starting $T_J=25^\circ\text{C}$, $I_d=I_{AR}$, $V_{dd}=40\text{V}$)	520	mJ

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0$	60			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$, $V_{DS} = \text{Max rating @ } 125^{\circ}\text{C}$			1 10	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{V}$, $I_D = 19\text{A}$		0.235	0.028	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$, $I_D = 19\text{ A}$		18		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25\text{V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$		980 225 80		pF pF pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 30\text{V}$, $I_D = 38\text{A}$ $V_{GS} = 10\text{V}$		32 6.5 12.7	58	nC nC nC

1. Pulsed: pulse duration=300 μs , duty cycle 1.5%

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time rise time	$V_{DD} = 30\text{ V}$, $I_D = 19\text{A}$, $R_G = 4.7\Omega$, $V_{GS} = 10\text{V}$ (see Figure 13)		12 40		ns ns
$t_{d(off)}$ t_f	Turn-off delay time fall time	$V_{DD} = 30\text{V}$, $I_D = 19\text{A}$, $R_G = 4.7\Omega$, $V_{GS} = 10\text{V}$ (see Figure 13)		28 10		ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				38	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				152	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 38A, V_{GS}=0$			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 38A$, $di/dt = 100A/\mu s$, $V_{DD} = 100V, T_J = 150^\circ C$ (see Figure 15)		49 100.5 4.1		ns μC A

1. Pulsed: pulse duration=300 μs , duty cycle 1.5%
2. Pulse width limited by safe operating area

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

Figure 2. Thermal impedance

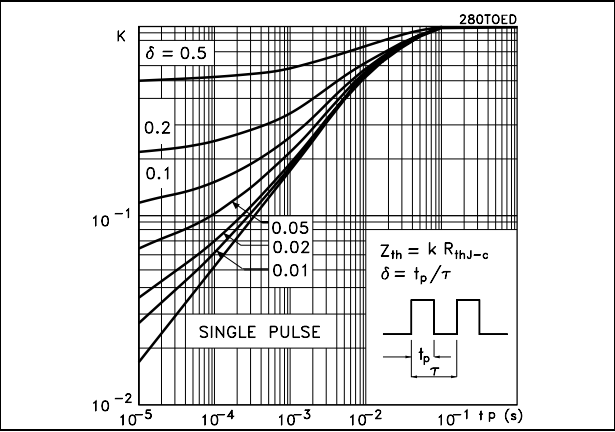
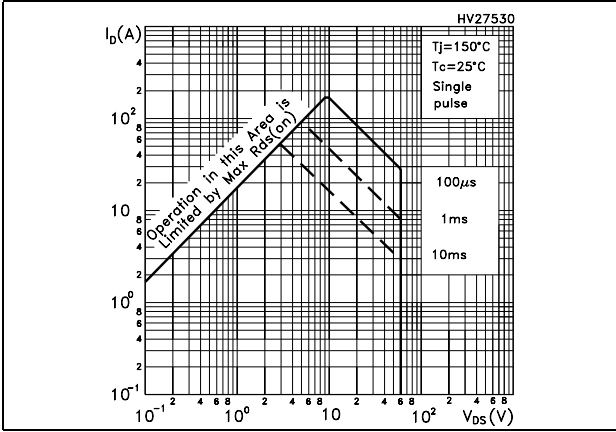


Figure 3. Output characteristics

Figure 4. Transfer characteristics

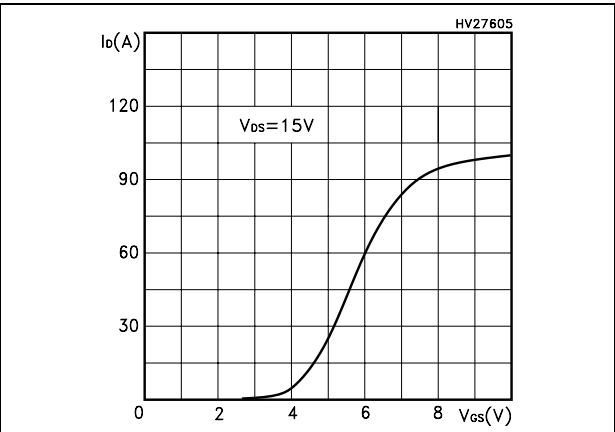
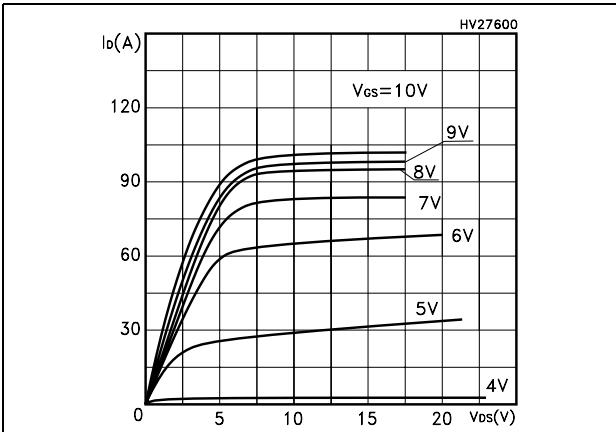


Figure 5. Transconductance

Figure 6. Static drain-source on resistance

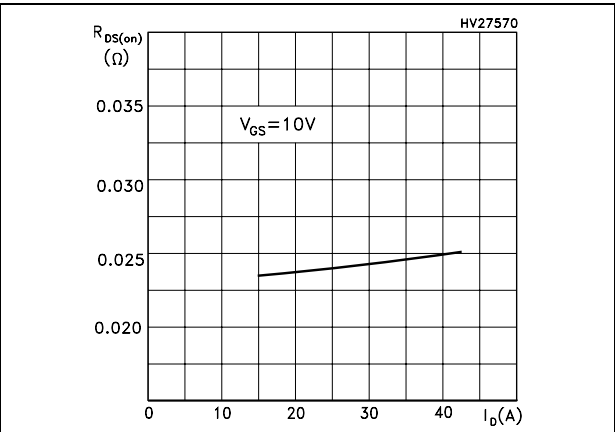
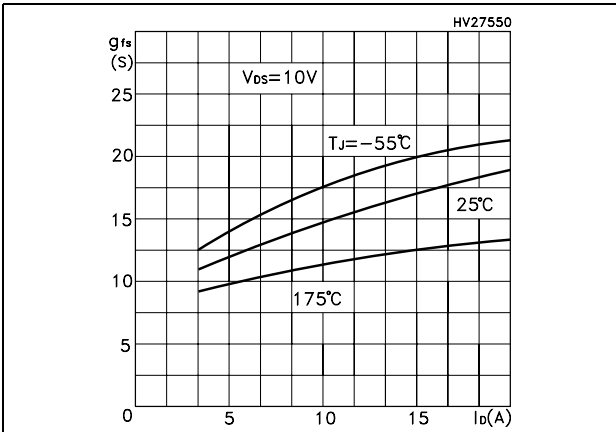


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

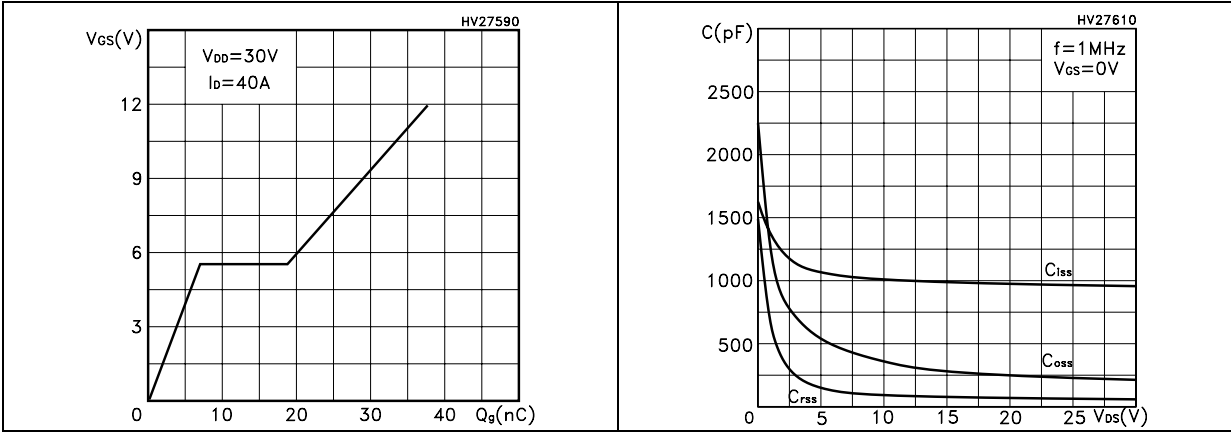


Figure 9. Normalized gate threshold voltage vs temperature Figure 10. Normalized on resistance vs temperature

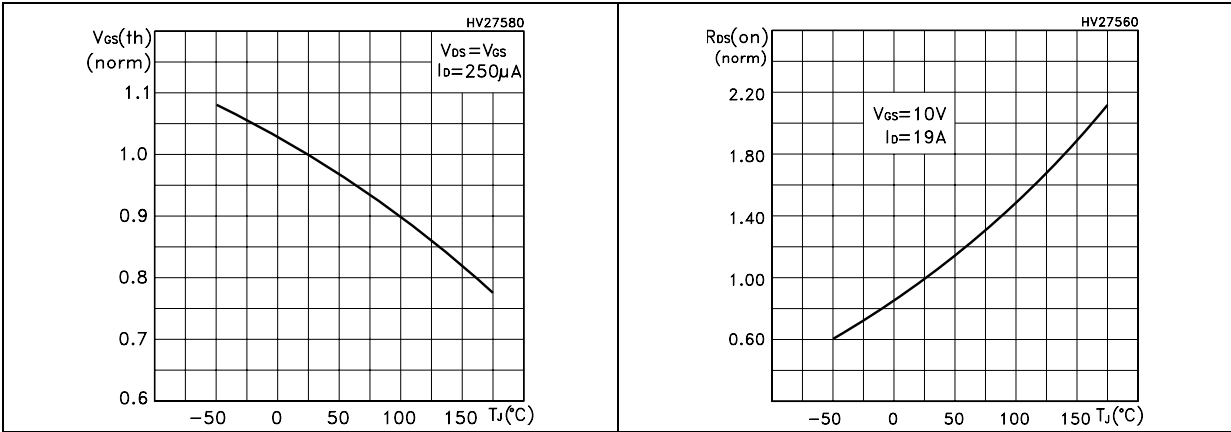
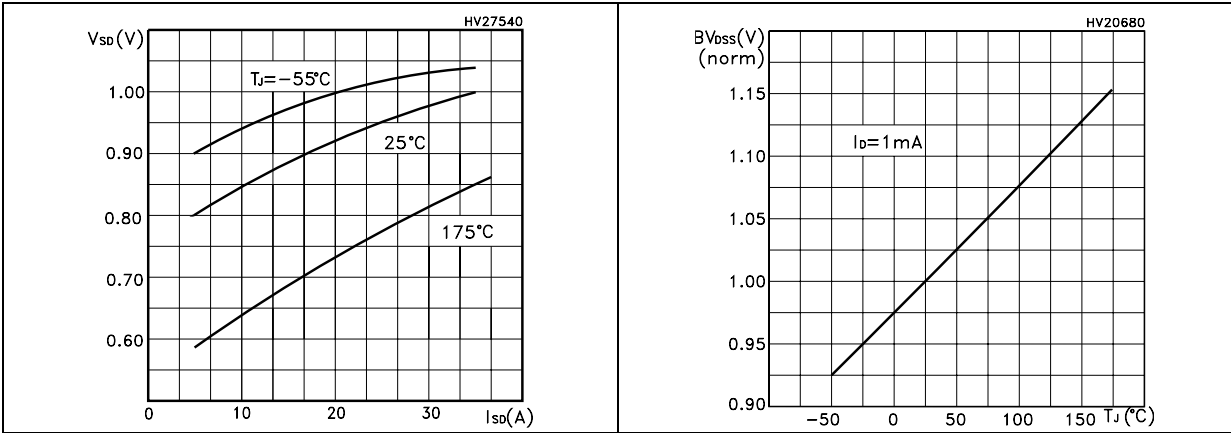


Figure 11. Source-drain diode forward characteristic Figure 12. Normalized breakdown voltage vs temperature



3 Test circuit

Figure 13. Switching times test circuit for resistive load

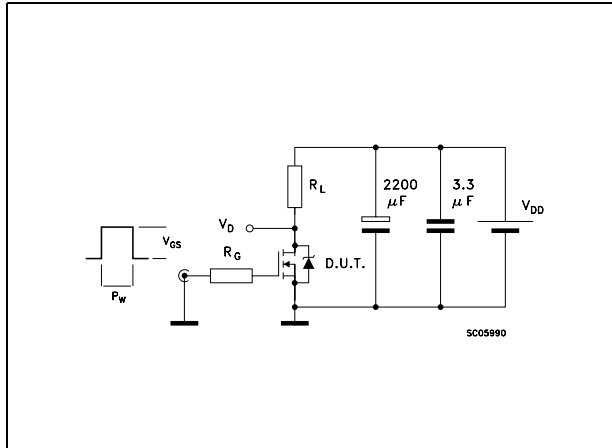


Figure 14. Gate charge test circuit

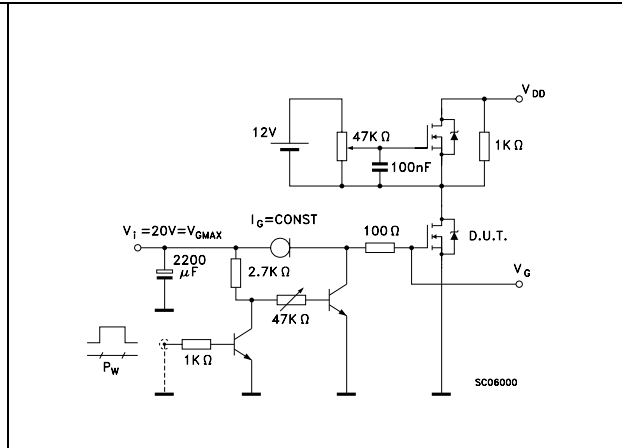


Figure 15. Test circuit for inductive load switching and diode recovery times

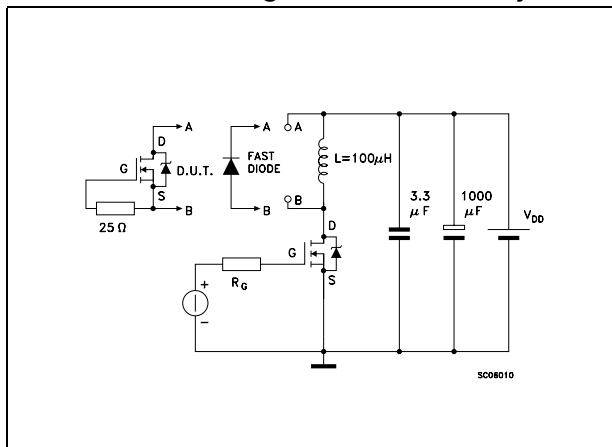


Figure 16. Unclamped Inductive load test circuit

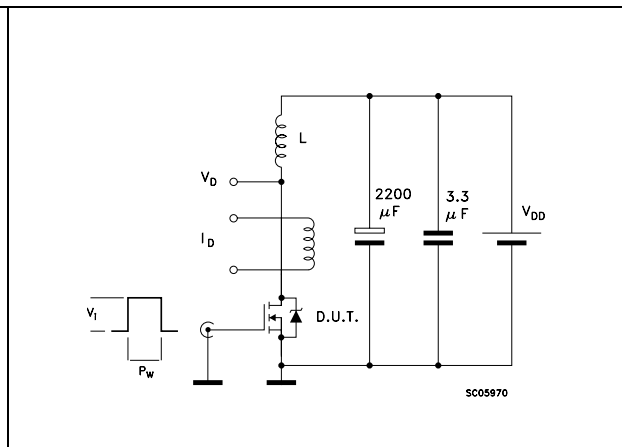


Figure 17. Unclamped inductive waveform

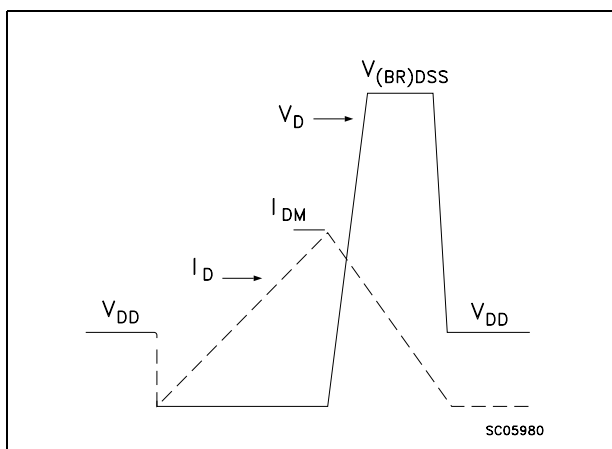
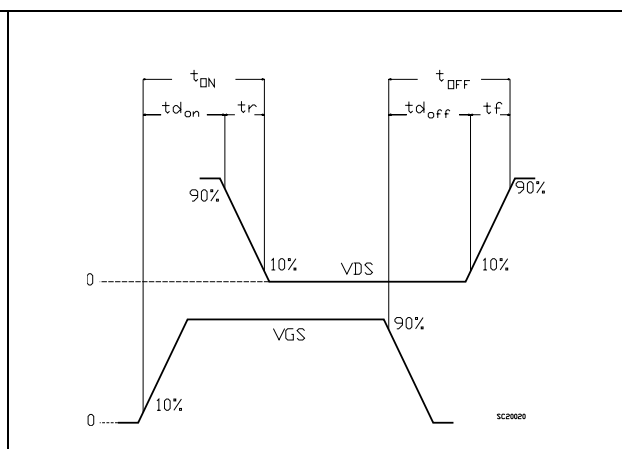


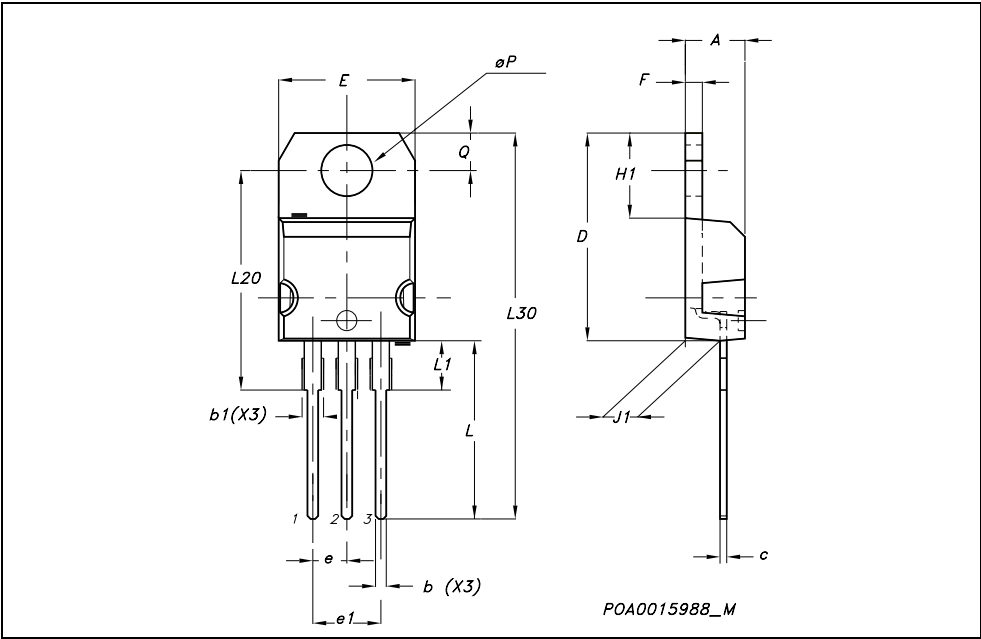
Figure 18. Switching time waveform



4 Package mechanical data

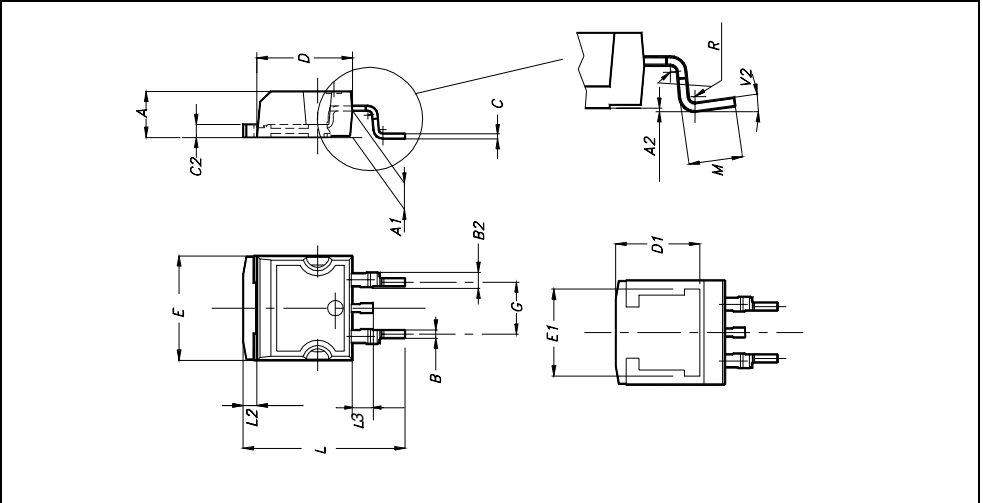
In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO-220 MECHANICAL DATA						
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



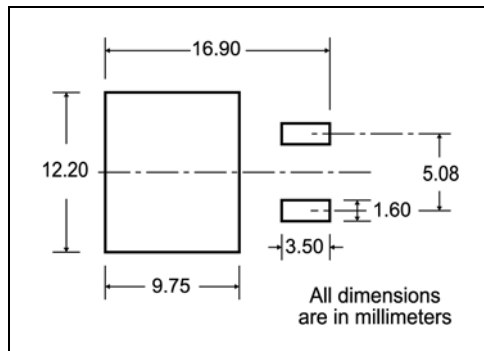
D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			

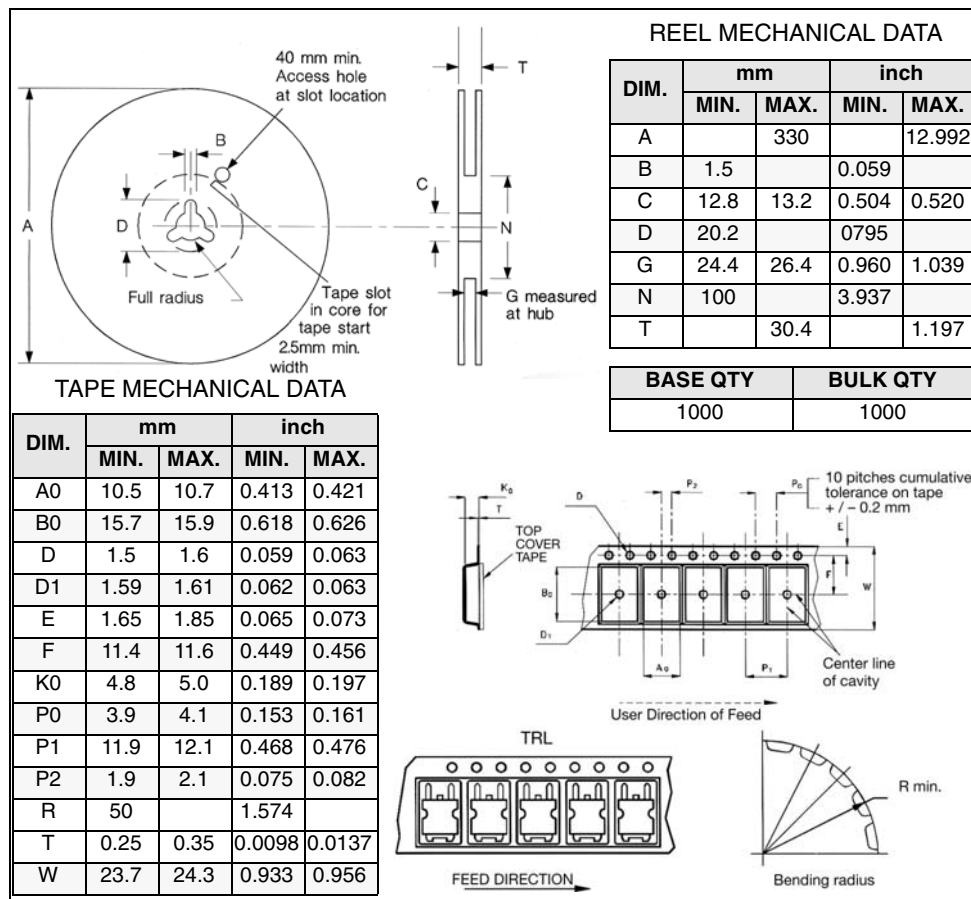


5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type

6 Revision history

Table 8. Revision history

Date	Revision	Changes
09-Sep-2004	1	Preliminary version
04-Feb-2005	2	Complete version
17-Aug-2006	3	New template. No content change
13-Nov-2006	4	Inserted new value

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